

C1 cont wherein an end portion of the second semiconductor film is provided inside an end portion of the second conductive film, and

wherein each of the first wiring and the second wiring has tapered inner and outer edges.

4. (Amended) A semiconductor device comprising:

a data wiring and a pixel electrode formed on an insulating surface;
barrier metal formed so as to correspond to the data wiring and the pixel electrode;

C2 a pair of first semiconductor films of one conductivity type formed on the barrier metal;

a second semiconductor film formed on and extending between the pair of first semiconductor films;

a gate insulating film formed on the second semiconductor film; and

a gate electrode formed on the gate insulating film,

wherein an end portion of the second semiconductor film is provided inside an end portion of the barrier metal, and

wherein each of the data wiring and the pixel electrode has tapered inner and outer edges.

30. (Amended) A semiconductor device comprising:

at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;

C3 a pair of first semiconductor films of one conductivity type formed over the first and second conductive films;

a second semiconductor film formed on and extending between the pair of first semiconductor films;

an insulating film including a gate insulating film formed on the second semiconductor film; and

a third conductive film including a gate electrode formed on the insulating film,

C3
C4
wherein each of the first and second conductive films and the pair of first semiconductor films has tapered inner and outer edges.

34. (Amended) A semiconductor device comprising:

at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;

a pair of first semiconductor films of one conductivity type formed over the first and second conductive films;

C4
a second semiconductor film formed on and extending between the pair of first semiconductor films;

an insulating film including a gate insulating film formed on the second semiconductor film; and

a third conductive film including a gate electrode formed on the insulating film,

wherein each of the pair of first semiconductor films and the second semiconductor film has tapered inner and outer edges and the pair of first semiconductor films extend beyond side edges of the second semiconductor film.

37. (Amended) A semiconductor device comprising:

at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;

C5
a pair of first semiconductor films of one conductivity type formed over the first and second conductive films;

a second semiconductor film formed on and extending between the pair of first semiconductor films;

an insulating film including a gate insulating film formed on the second semiconductor film; and

a third conductive film including a gate electrode formed on the insulating film,

C5
would
wherein each of the second semiconductor film and the third conductive film has tapered inner and outer edges and the second semiconductor film extends beyond side edges of the third conductive film.

40. (Amended) A semiconductor device comprising:

at least first and second conductive films formed on an insulating surface wherein the first and second conductive films are separated from each other;

a pair of barrier metal layers formed on the first and second conductive films wherein said barrier metal layers have a tapered outer edge;

a pair of first semiconductor films of one conductivity type formed on the pair of barrier metal layers, respectively, wherein each of the ^{pair of} first semiconductor films has a tapered outer edge;

C6
a second semiconductor film formed on and extending between the pair of first semiconductor films wherein the second semiconductor film has a tapered outer edge;

an insulating film including a gate insulating film formed on the second semiconductor film; and

a third conductive film including a gate electrode formed on the insulating film wherein said third conductive film has a tapered outer edge,

wherein said insulating film extends beyond the outer edge of the third conductive film, and said second semiconductor film extends beyond an outer edge of the insulating film,

wherein each of the first conductive film and the second conductive film has tapered inner and outer edges.
